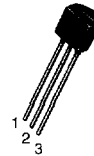
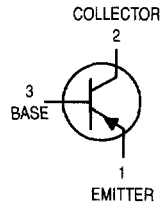


High Voltage Transistors

PNP Silicon

BF421
BF423



CASE 29-04, STYLE 14
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	BF421	BF423	Unit
Collector-Emitter Voltage	V_{CEO}	-300	-250	Vdc
Collector-Base Voltage	V_{CBO}	-300	-250	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0		Vdc
Collector Current — Continuous	I_C	-500		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (1) ($I_C = -1.0$ mAdc, $I_E = 0$)	BF421 BF423	$V_{(BR)CEO}$	-300 -250	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = -100$ μ Adc, $I_E = 0$)	BF421 BF423	$V_{(BR)CBO}$	-300 -250	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = -100$ μ Adc, $I_C = 0$)	BF421 BF423	$V_{(BR)EBO}$	-5.0 -5.0	— —	Vdc
Collector Cutoff Current ($V_{CB} = -200$ Vdc, $I_E = 0$)	BF421 BF423	I_{CBO}	— —	-0.01 —	μ Adc
Emitter Cutoff Current ($V_{EB} = -5.0$ Vdc, $I_C = 0$)	BF421 BF423	I_{EBO}	— —	-100 —	nAdc

1. Pulse Test: Pulse Width ≤ 300 μ s; Duty Cycle $\leq 2.0\%$.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = -25\text{ mA}$, $V_{CE} = -20\text{ Vdc}$)	h_{FE}	50	—	—
	BF421	50	—	—
	BF423	—	—	—
Collector–Emitter Saturation Voltage ($I_C = -20\text{ mAdc}$, $I_B = -2.0\text{ mAdc}$)	$V_{CE(\text{sat})}$	—	-0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$)	$V_{BE(\text{sat})}$	—	-2.0	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = -10\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$, $f = 20\text{ MHz}$)	f_T	60	—	MHz
Common Emitter Feedback Capacitance ($V_{CB} = -30\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{re}	—	2.8	pF

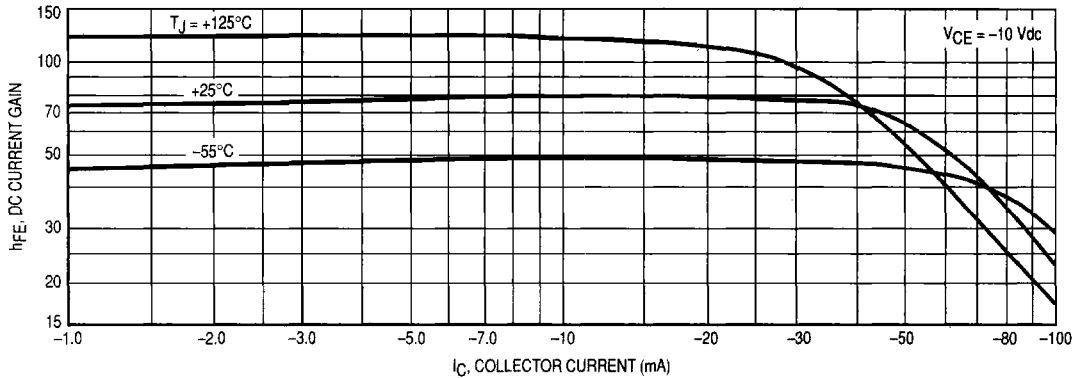


Figure 1. DC Current Gain

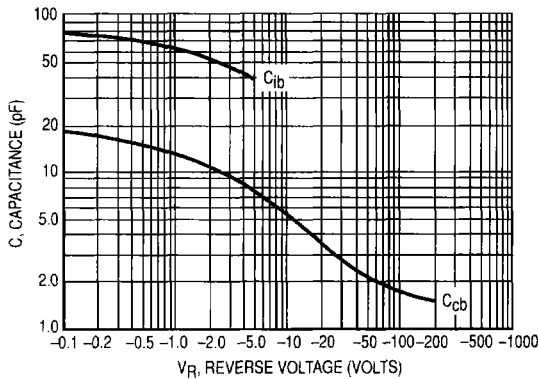


Figure 2. Capacitances

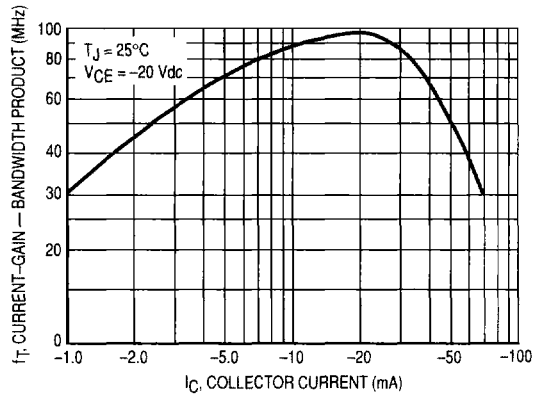


Figure 3. Current-Gain — Bandwidth Product

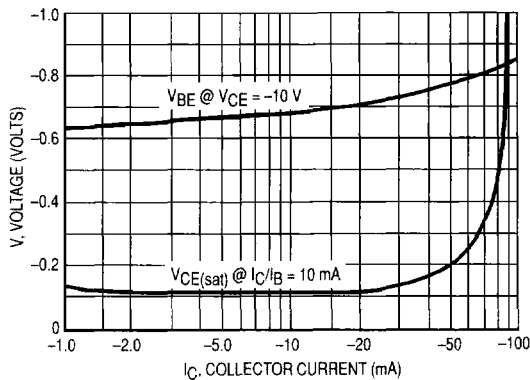


Figure 4. "On" Voltages

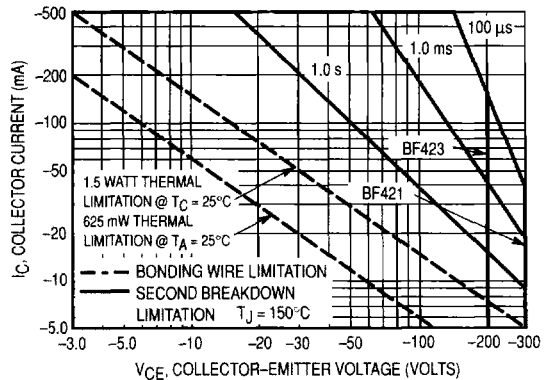


Figure 5. Active Region — Safe Operating Area